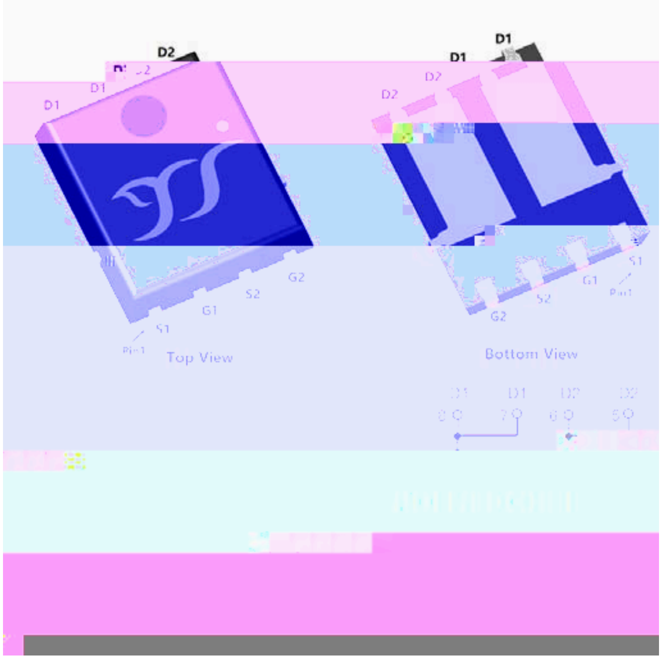
N-Channel and N-Channel Complementary MOSFET



Product Summary

- V_{DS} 40V
- I_D 70A
- $R_{DS(ON)}$(at V_{GS}=10V) 5.3mΩ
- 100% EAS Tested
- 100% V_{DS} Tested

General Description

- Excell] ̂ a a " =25 Ņ unless otherwise noted)

Parameter			Symbol	Limit	Unit
Drain-source Voltage			V_{DS}	40	V
Gate-source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25 -	I_D	16	A
		T_A=100 -		11	
Continuous Drain Current (Note 1,3)	Steady-State	T_C=25 -		70	
		T_C =100 -		49	
Pulsed Drain Current	T_C=25 , t_P=100µs		I_{DM}	250	A
Avalanche energy	V_G=10V, R_G=25Ω, L=0.5mH, IAS=14A		EAS	49	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25 -	P_D	2.5	W
		T_A=100 -		1.25	
Total Power Dissipation (Note 1,3)	Steady-State	T_C=25 -		50	
		T_C =100 -		25	
Junction and Storage Temperature Range			T_J ,T_{STG}	-55 +175	-

Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	50	60	- /W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	2.5	3	

■ **Ordering Information** (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJGD5D3G04HQ	F1	YJGD5D3G04H	5000	10000	100000	13“ reel

■Typical Electrical and Thermal Characteristics Diagrams

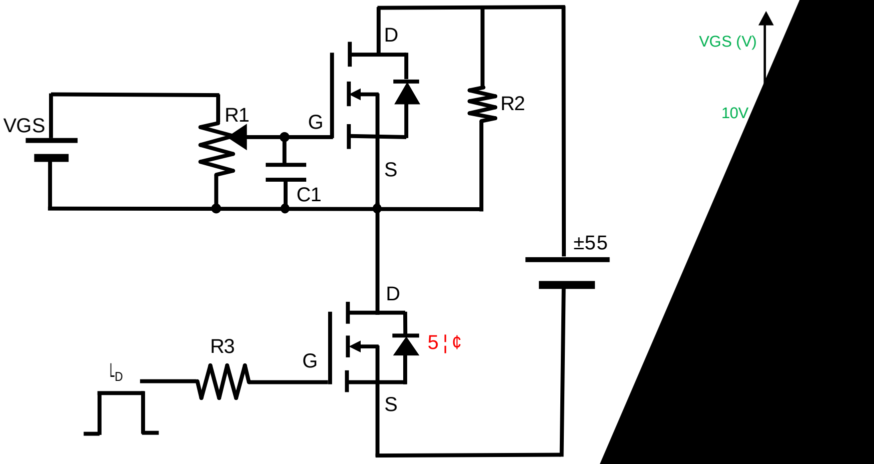
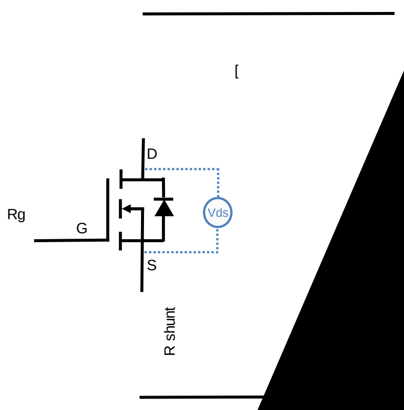
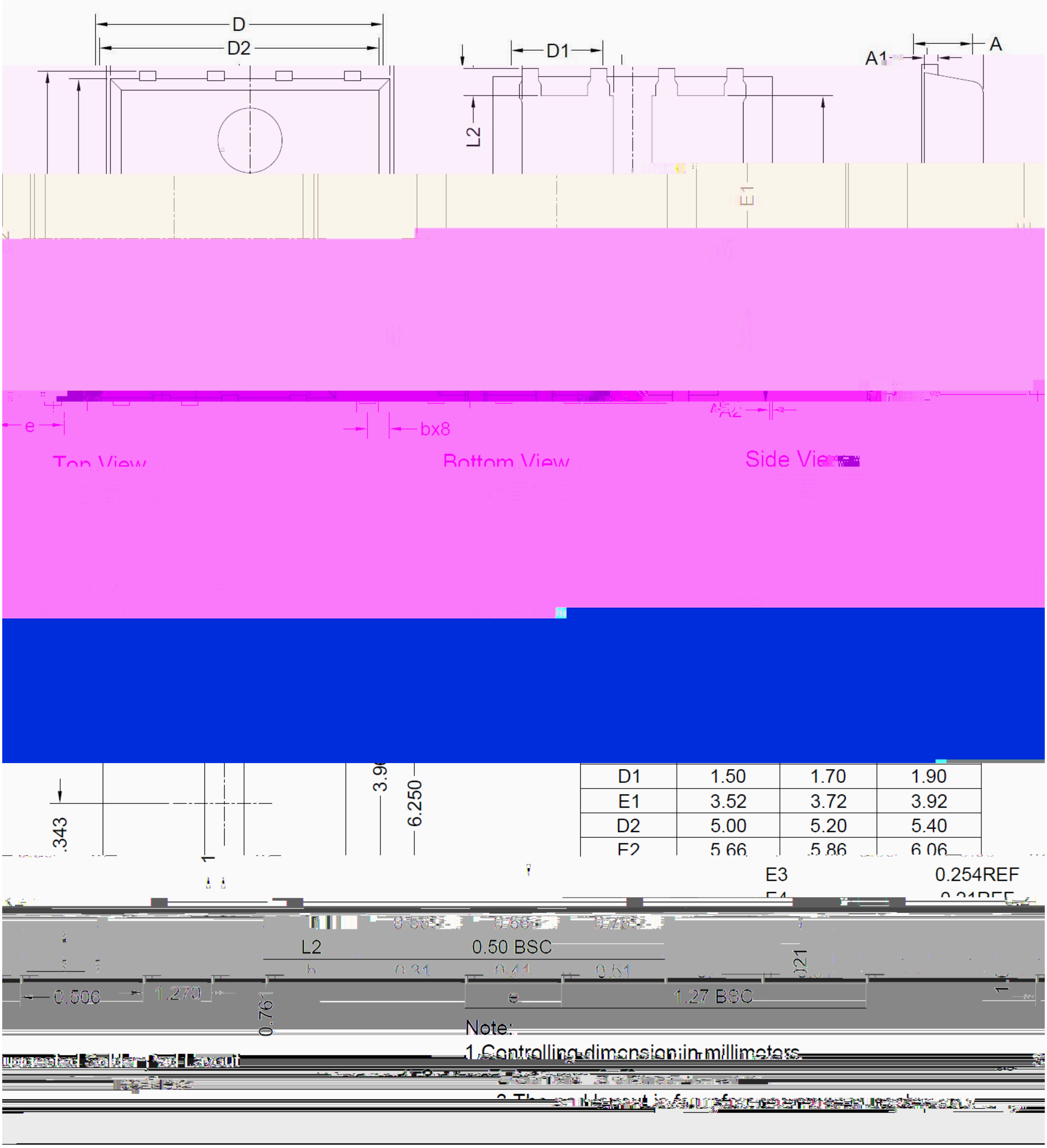


Figure B. Gat



L J X U H %

■ PDFN5060-8L-E-1.1mm Package information



D1	1.50	1.70	1.90
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254REF		
[illegible]	0.560	0.660	0.760
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1.Controlling dimension:in millimeters.

2.[illegible]

3.The pad layout is for reference purposes only.